

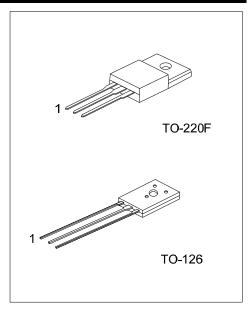
## 2SC4793

## NPN SILICON TRANSISTOR

# NPN SILICON TRANSISTOR

## FEATURES

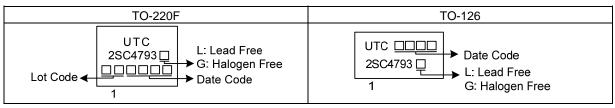
\*High transition frequency \*Power amplifier applications \*Driver stage amplifier applications



### ORDERING INFORMATION

Order Number		Dookogo	Pin Assignment			Dooking	
Lead Free	Halogen Free	Package	1	2	3	Packing	
2SC4793L-x-TF3-T	2SC4793G-x-TF3-T	TO-220F	В	С	Е	Tube	
2SC4793L-x-T60-K	2SC4793G-x-T60-K	TO-126	E C		В	Bulk	
Note: Pin Assignment: B: Bas	Note: Pin Assignment: B: Base C: Collector E: Emitter						
2SC4793G-x-TF3-T (1)Packing Type (2)Package Type (3)Rank (4)Green Package		(1) T: Tube, K: Bulk (2) TF3: TO-220F, T60: TO-126 (3) refer to Classification of h <sub>FE</sub> (4) G: Halogen Free and Lead Free, L: Lead Free					

#### MARKING



## ■ **ABSOLUTE MAXIMUM RATINGS** (T<sub>A</sub>=25°C, unless others specified)

PARAMETER		SYMBOL	RATINGS	UNIT	
Collector-Base Voltage		V <sub>CBO</sub>	230	V	
Collector-Emitter Voltage		V <sub>CEO</sub>	230	V	
Emitter-Base Voltage		V <sub>EBO</sub>	5	V	
Collector Current		Ιc	1	А	
Base Current		I <sub>B</sub>	0.1	А	
Collector Power Dissipation	T <sub>A</sub> =25°C	TO-220F	Pc	2.0	W
		TO-126		1.4	W
	$T_{c}=25^{\circ}C$	TO-220F		20	W
		TO-126		16	W
Junction Temperature		ΤJ	+150	°C	
Storage Temperature Range		T <sub>STG</sub>	-55 ~ +150	°C	

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

#### ■ ELECTRICAL CHARACTERISTICS (T<sub>A</sub>=25°C, unless others specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-Emitter Breakdown Voltage	BV <sub>CEO</sub>	I <sub>C</sub> =10mA, I <sub>B</sub> =0	230			V
Base -Emitter Voltage	V <sub>BE</sub>	V <sub>CE</sub> =5V, I <sub>C</sub> =500mA			1.0	V
Collector-Emitter Saturation Voltage	V <sub>CE(SAT)</sub>	I <sub>C</sub> =500mA, I <sub>B</sub> =50mA			1.5	V
Collector Cut-off Current	I <sub>CBO</sub>	V <sub>CB</sub> =230V, I <sub>E</sub> =0			1.0	μA
Emitter Cut-off Current	I <sub>EBO</sub>	V <sub>EB</sub> =5V, I <sub>C</sub> =0			1.0	μA
DC Current Gain	h <sub>FE</sub>	V <sub>CE</sub> =5V, I <sub>C</sub> =100mA	100		320	
Transition Frequency	f⊤	V <sub>CE</sub> =10V, I <sub>C</sub> =100mA		100		MHz
Collector Output Capacitance	Cob	V <sub>CB</sub> =10V, I <sub>E</sub> =0, f=1MHz		20		рF

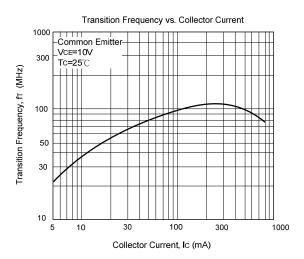
## CLASSIFICATION OF h<sub>FE</sub>

RANK	А	В
RANGE	100-200	180-320

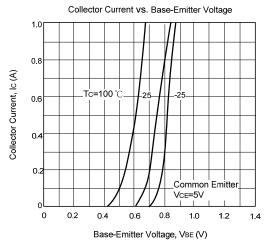


# 2SC4793

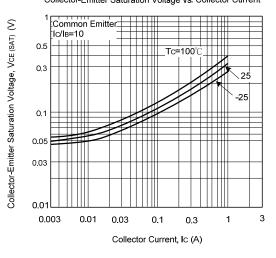
## NPN SILICON TRANSISTOR

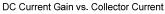


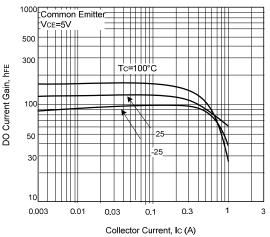
#### TYPICAL CHARACTERISTICS

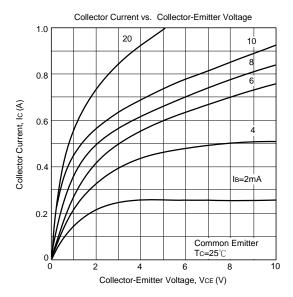


Collector-Emitter Saturation Voltage vs. Collector Current

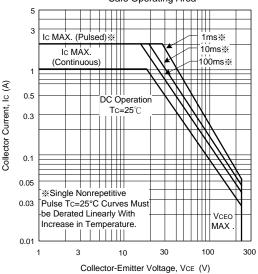














UTC assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all UTC products described or contained herein. UTC products are not designed for use in life support appliances, devices or systems where malfunction of these products can be reasonably expected to result in personal injury. Reproduction in whole or in part is prohibited without the prior written consent of the copyright owner. UTC reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.

